



Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-50V	1.7Ω@-10V	-0.13A
	1.9Ω@-5V	

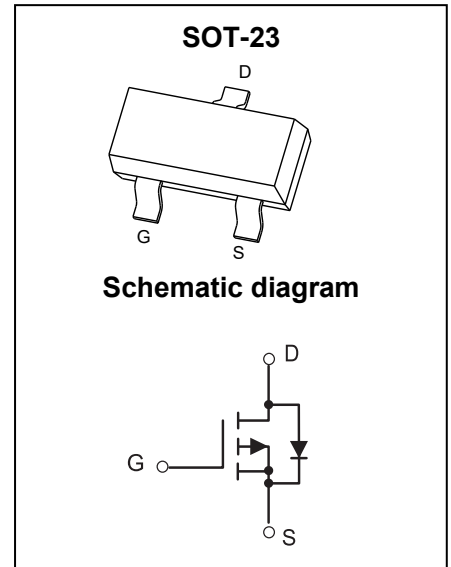
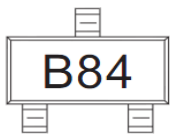
Feature

- Trench Technology MOSFET
- Low Gate Charge

Application

- Load Switch for Portable Devices
- DC/DC Converter

MARKING:



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain - Source Voltage	V_{DS}	-50	V
Gate - Source Voltage	V_{GS}	±20	V
Continuous Drain Current ¹	I_D	-0.13	A
Pulsed Drain Current ²	I_{DM}	-1.2	A
Power Dissipation ⁴	P_D	300	mW
Thermal Resistance from Junction to Ambient ⁵	$R_{\theta JA}$	417	°C/W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55~ +150	°C

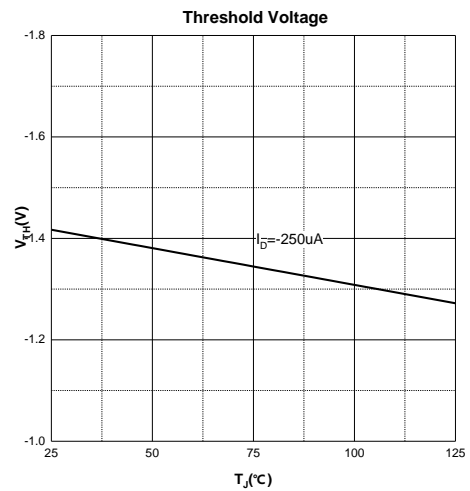
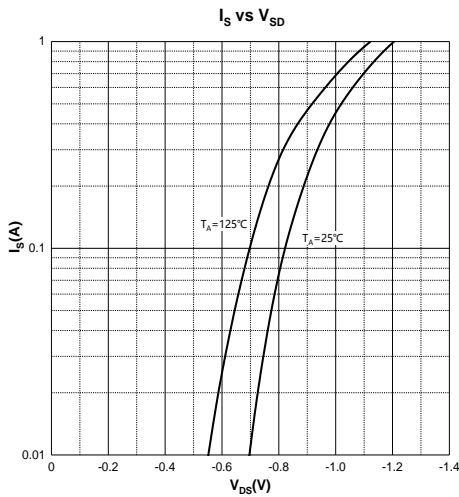
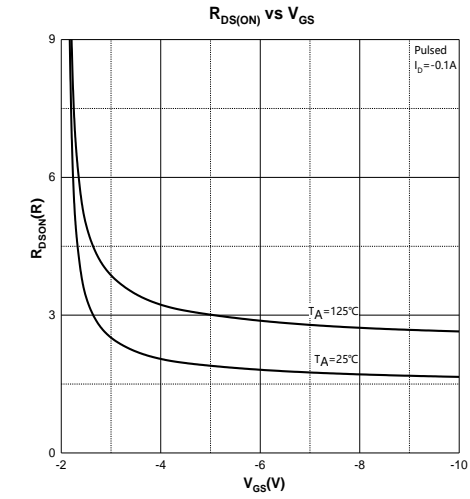
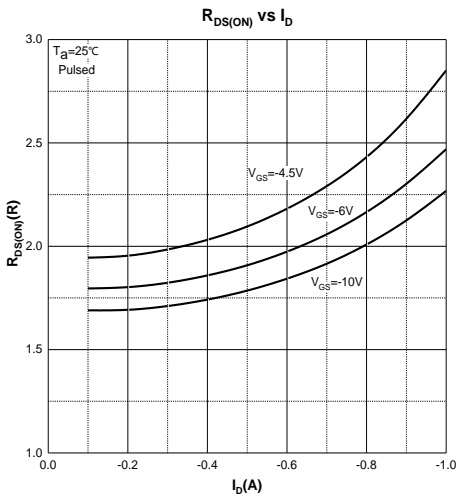
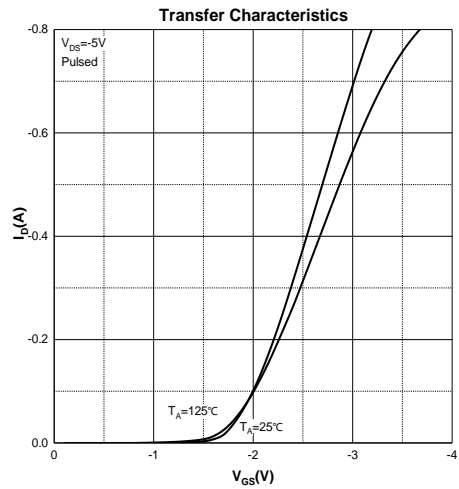
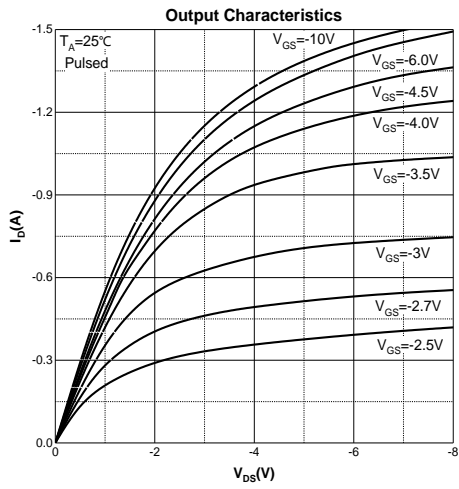
MOSFET ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain – Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-50			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -50V, V_{GS} = 0V$			-1	μA
Gate – Body Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
On Characteristics³						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.9	-1.4	-2.0	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -0.1A$		1.7	5	Ω
		$V_{GS} = -4.5V, I_D = -0.1A$		1.9	6	
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = -25V, V_{GS} = 0V, f = 1MHz$		32.9		pF
Output Capacitance	C_{oss}			5.48		
Reverse Transfer Capacitance	C_{rss}			3.31		
Gate Resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		73		Ω
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DS} = -10V, V_{GS} = -10V, I_D = -0.1A$		0.62		nC
Gate-source Charge	Q_{gs}			0.13		
Gate-drain Charge	Q_{gd}			0.11		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = -30V, V_{GS} = -10V,$ $R_L = 110\Omega, R_G = 50\Omega$		11		ns
Turn-on Rise Time	t_r			6		
Turn-off Delay Ttime	$t_{d(off)}$			19		
Turn-off Fall Ttime	t_f			8		
Source - Drain Diode Characteristics						
Diode Forward Voltage ³	V_{SD}	$V_{GS} = 0V, I_S = -0.1A$			-1.2	V

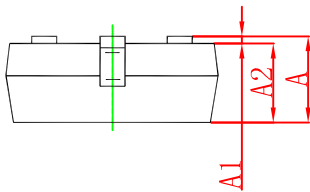
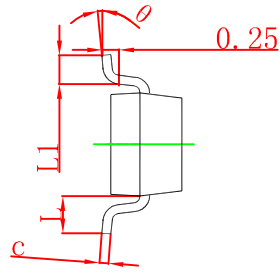
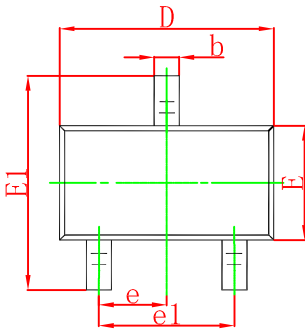
Notes :

- 1.The maximum current rating is limited by Chip.
- 2.Pulse Test : Pulse Width $\leq 10\mu s$, duty cycle $\leq 1\%$.
- 3.Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 4.The power dissipation P_D is limited by $T_{J(MAX)} = 150^\circ\text{C}$.
- 5.Device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

Typical Characteristics



SOT-23 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

单击下面可查看定价，库存，交付和生命周期等信息

[>>GP\(格瑞宝\)](#)